

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yi-Fan Chen, Examiner: Huynh, Andy
5 Chi-King Pu,
Shou-Kong Fan
Filing Date: 04/18/01 Art Unit: 2818
Serial No.: 09/836,258 Docket No.: NAUP0280USA

10. Title: BYPASS CIRCUITS FOR REDUCING PLASMA DAMAGE

To: The Commissioner of Patents and Trademarks
Washington, D.C. 20231

15 Subject: Response to the Office Action dated 05/03/2002

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Dear Sir:

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AMENDMENT

TECHNOLOGY CENTER 2800

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In response to the Office Action identified above, please amend the above-identified application as follows:

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In the claims:

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1. (Once amended) A bypass circuit for reducing plasma damage to a gate oxide of a metal-oxide semiconductor (MOS) wafer, the bypass circuit positioned on a semiconductor wafer, the semiconductor wafer comprising a substrate, the MOS transistor, a dielectric layer, and the bypass circuit, respectively, with the bypass circuit comprising: